

PATENT APPLICATION

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	APPLICANT	TANIZAWA	
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REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
AD	4,576,052 (Discussed on page 2 of the spec. and corresponding to JP-B2-3-67211)	Mar. 18, 1986	Sugiyama	—	—
I	5,042,307 (Discussed on page 3 of the spec. and corresponding to JP-A-3-51733)	Aug. 27, 1991	Kato	—	—

FOREIGN PATENT DOCUMENTS

								TRANSLATION	
		DOCUMENT NUMBER	DATE	COUNTRY	NAME	CLASS	SUB CLASS	YES	NO
Ad		JP-B2-3-67211 ~	10/22/91	JAPAN		—	—	X	
		JP-A-3-51733 ~	3/6/91	JAPAN		—	—	X	
		JP-A-4-25767 ~ (Corresponding to JP Patent No. 2976487 which is discussed on page 1 of the spec.)	1/29/92	JAPAN		—	—	X	
		JP-A-63-173933 ~	7/18/88	JAPAN		—	—	X	
		JP-A-4-2170 ~	1/7/92	JAPAN		—	—	X	
		JP-A-60-144632 ~	7/31/85	JAPAN		—	—	X	
		JP-B2-62-55629 ~	11/20/87	JAPAN		—	—	X	
		JP-A-3-68830 ~	3/25/91	JAPAN		—	—	X	
		JP-A-4-89541 ~	3/23/92	JAPAN		—	—	X	
		JP-A-57-58791 ~	12/11/82	JAPAN		—	—	X	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

AD	Sugiyama et al., "Nonlinear Temperature Characteristics in Silicon Piezoresistive Pressure Sensors," <u>Proceedings of the 5th Sensor Symposium</u> , 1985, pp.103-107.
EXAMINER	AD 46
DATE CONSIDERED	12/2/02

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